October 20 (Tue.), 2026

[Oral 01] CMP for Advanced Interconnects (I)

09:55-11:20

International Conference Hall (B1F)

● Session Chair: Patrick Ong (imec, Belgium)

09:55-10:20 [Oral 01-1]	**[Invited]** CMP Process Innovations, Growing Needs and Challenges Imposed by New Architectures, New Materials and Dimensional Scaling for Logic and Advanced Interconnects Nancy Heylen (imec, Belgium)
10:20-10:40 [Oral 01-2]	Research on CMP Slurry for Removal Rate and Defect Control for Sub-10nm Node Semiconductors Jong-Young Cho (SK hynix Inc., Korea), Deok-Su Han (YCChem Co., Ltd., Korea), Woojoo Kim (SK hynix Inc., Korea), and Hyun-goo Kang (SK hynix Inc., Korea)
10:40-11:00 [Oral 01-3]	Advanced Tungsten Slurry with Low Etching Rate, High W / Oxide Selectivity, and E-O-E Free Topography Sanghwan Kim, Guo Yi (Qnity Electronics, Inc., USA), Joseph Sung, and Allison Hsu (Qnity Electronics, Inc., Taiwan)
11:00-11:20 [Oral 01-4]	Innovative Solution for High Throughput Density Tungsten CMP Through In-situ Conditioning Development Zhengqiu Sun, Wern Jun Mak (Micron SemiAsiaOP Pte Ltd, Singapore), and Arvin Chang (Micron Memory Taiwan Co., Taiwan)